

# Keshuang Li

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/10461492/publications.pdf>

Version: 2024-02-01

8  
papers

105  
citations

1684188

5  
h-index

1872680

6  
g-index

8  
all docs

8  
docs citations

8  
times ranked

118  
citing authors

| # | ARTICLE   | IF  | CITATIONS |
|---|---|-----|-----------|
| 1 | The role of different types of dopants in 1.3 $\mu\text{m}$ InAs/GaAs quantum-dot lasers. Journal Physics D: Applied Physics, 2022, 55, 215105. | 2.8 | 6         |
| 2 | All-MBE grown InAs/GaAs quantum dot lasers with thin Ge buffer layer on Si substrates. Journal Physics D: Applied Physics, 2021, 54, 035103.    | 2.8 | 23        |
| 3 | Inversion Boundary Annihilation in GaAs Monolithically Grown on On-axis Silicon (001). Advanced Optical Materials, 2020, 8, 2000970.            | 7.3 | 22        |
| 4 | Impact of ex-situ annealing on strain and composition of MBE grown GeSn. Journal Physics D: Applied Physics, 2020, 53, 485104.                  | 2.8 | 4         |
| 5 | Thin Ge buffer layer on silicon for integration of III-V on silicon. Journal of Crystal Growth, 2019, 514, 109-113.                             | 1.5 | 17        |
| 6 | O-band InAs/GaAs quantum dot laser monolithically integrated on exact (001) Si substrate. Journal of Crystal Growth, 2019, 511, 56-60.          | 1.5 | 31        |
| 7 | InAs/GaAs Quantum Dot Lasers Monolithically Integrated on Group IV Platform. , 2018, , .  |     | 1         |
| 8 | GaAs Compounds Heteroepitaxy on Silicon for Opto and Nano Electronic Applications. , 0, , .   |     | 1         |